

FORM PTO 1449 (modified)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)		ATTY DOCKET NO. <b>35.C12475 Div. I</b>		APPLICATION NO. <b>Div. of 08/999,1328</b>		JCS31 U.S. PAT. 09/638398	
APPLICANT <b>KATSUMI NAKAGAWA ET AL.</b>		FILING DATE <b>Herewith</b>		GROUP <b>2812</b>			

  

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
SM	4,778,478	10/18/88	Barnett	437	5		
	5,536,361	7/16/96	Kondo et al.	156	630.1		
	4,774,194	9/27/88	Hokuyou	437	5		
	4,058,418	11/15/77	Lindmayer	148	175		
	5,856,229	1/5/99	Sakaguchi et al.	438	406		
	5,966,620	10/12/99	Sakaguchi et al.	438	455		
	5,492,859	2/20/96	Sakaguchi et al.	437	86		
SM	5,840,616	11/24/98	Sakaguchi et al.	438	459		

  

FOREIGN PATENT DOCUMENTS							
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT		
7-302889	11/14/95	Japan			abstract		
8-97389	4/12/96	Japan			abstract		
8-213645	8/20/96	Japan			abstract		
5-211128	8/20/93	Japan			abstract		
6-191987	7/12/94	Japan			abstract		

  

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)	
SM	H. Baumgart, et al., "Dielectric Isolation Using Porous Silicon", Mat. Res. Soc. Symp. Proc., vol. 33, pp. 63-68 (1994).
P	Nikkei Microdevices, pp. 76-77 (1994).
P	P. Schmuki, et al., "Initiation and Formation of Porous GaAs", J. Electrochem. Soc., vol. 143, no. 10, pp. 3316-3322 (1996).
P	T. Unagami, "Formation Mechanism of Porous Silicon Layer by Anodization in HF Solution", J. Electrochem. Soc., vol. 127, no. 2, pp. 476-483 (1980).
P	R.P. Holmstrom, et al., "Composite dielectric isolation by highly selective and self-stopping formation of oxidized porous silicon", Appl. Phys. Lett., vol. 42, no. 4, pp. 386-388 (1983).
SM	A.G. Mills, et al., "Peelable Film Technology for Solar Cells", 11 <sup>th</sup> IEEE Photovoltaic Spec. Conf., Scottsdale, Arizona, pp. 338-341 (1975).

  

EXAMINER	DATE CONSIDERED
SM	12/29/00

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO 1449 (modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)				ATTY DOCKET NO. <b>35.C12475 Div. I</b>		APPLICATION NO. <b>Div. of 08/999,132</b>	
				APPLICANT <b>KATSUMI NAKAGAWA ET AL.</b>			
				FILING DATE <b>Herewith</b>		GROUP <b>2812</b>	

  

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
<i>San</i> <div style="border-left: 1px solid black; height: 100px; margin: 0 auto; width: 20px;"></div>	5,277,748	1/11/94	Sakaguchi et al.	156	630	<div style="display: flex; align-items: center;"> <div style="writing-mode: vertical-rl; transform: rotate(180deg); font-size: small;">09/15/00</div> <div style="writing-mode: vertical-rl; transform: rotate(180deg); font-size: small;">09/638398</div> </div>	
	5,811,348	9/22/98	Matsushita et al.	438	455		
	5,391,257	2/21/95	Sullivan et al.	156	630		
	5,371,037	12/6/94	Yonehara	437	86		
	4,816,420	3/28/89	Bozler et al.	437	2		
<i>San</i>	5,374,564	12/20/94	Bruel	437	24		

  

FOREIGN PATENT DOCUMENTS							
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT		
<i>San</i> <div style="border-left: 1px solid black; height: 100px; margin: 0 auto; width: 20px;"></div>	5-21338	1/29/93	Japan	—	abstract		
	0 688 048	12/20/95	EP	—			
	0 272 636	06/29/88	EP	—			
	0 703 609	3/27/96	EP	—	abstract		
	81/02948	10/15/81	PCT	—			
<i>San</i>	6-45622	2/18/94	Japan	—	abstract		

  

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)		

  

EXAMINER <i>San</i>	DATE CONSIDERED <i>12/29/00</i>
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